

Silicon PNP Power Transistors

2SB731

DESCRIPTION

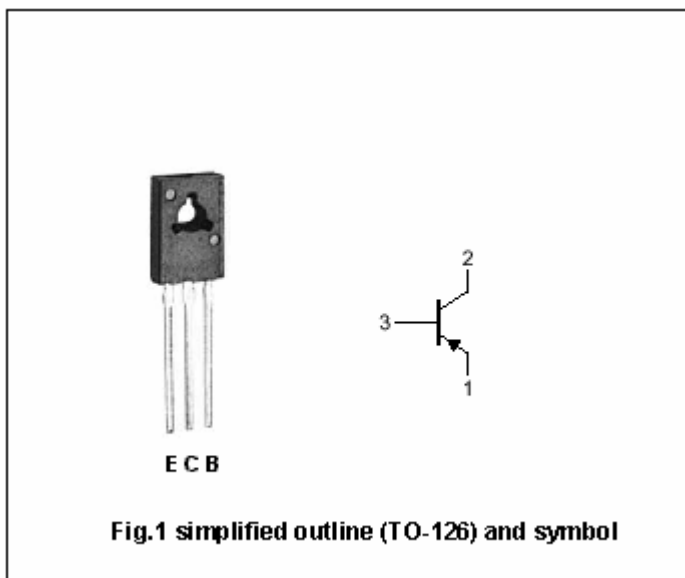
- With TO-126 package
- Complement to type 2SD809
- Low collector saturation voltage

APPLICATIONS

- Audio frequency power amplifier
- Low speed switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-60	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current (DC)		-1	A
I _{CM}	Collector current-Peak		-2	A
I _B	Base current (DC)		-0.5	A
P _T	Total power dissipation	T _a =25°C	1.0	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.0A; I _B =-50mA		-0.5	-0.6	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.0A; I _B =-50mA		-1.0	-1.2	V
I _{CB0}	Collector cut-off current	V _{CB} =-50V; I _E =0			-0.1	μA
I _{EB0}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	μA
h _{FE-1}	DC current gain	I _C =-0.1A; V _{CE} =-2V	135		600	
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-1V	40			
f _T	Transition frequency	I _C =-10mA; V _{CE} =-2V		75		MHz
C _{OB}	Collector output capacitance	I _E =0; f=1MHz; V _{CB} =-10V		25		pF

◆ h_{FE-1} Classifications

L	K	F	E
135-270	200-400	300-480	360-600

PACKAGE OUTLINE

